DRAF114T

Silicon PNP epitaxial planar type

For digital circuits
Complementary to DRCF114T
DRA3114T in ML3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

■ Packaging

DRAF114T0L Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	–50	V
Collector-emitter voltage (Base open)	V_{CEO}	–50	V
Collector current	I_C	–100	mA
Total power dissipation *	P_T	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

Note) *: Copper plate at the collector is 5.0 mm^2 on substrate at 10 mm × 12 mm × 0.8 mm.

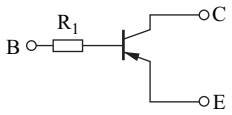
■ Package

- Code
  ML3-N4-B
  Package dimension clicks here.→ Click!

- Pin Name
  1: Base
  2: Emitter
  3: Collector

■ Marking Symbol: LD

■ Internal Connection



Resistance value	R_1	10	kΩ

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = –10$ μA, $I_E = 0$	–50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = –2$ mA, $I_B = 0$	–50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = –50$ V, $I_E = 0$			– 0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = –50$ V, $I_B = 0$			– 0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = –6$ V, $I_C = 0$			– 0.01	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = –10$ V, $I_C = –5$ mA	160		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = –10$ mA, $I_B = – 0.5$ mA			– 0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = – 0.2$ V, $I_C = –5$ mA	–1.2			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = –5$ V, $I_C = –100$ μA			– 0.4	V
Input resistance	R_1		–30%	10	+30%	kΩ

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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